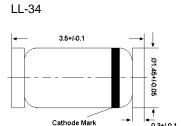
Silicon Epitaxial Planar Switching Diode

Features

- Fast switching speed
- High reliability
- High conductance
- For general purpose switching applications



Glass case MiniMELF Dimensions in mm

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	50	V
Average Rectified Forward Current	I _{F(AV)}	300	mA
Forward Continuous Current	I _{FM}	400	mA
Power Dissipation	P _{tot}	500	mW
Junction Temperature	T _j	175	°C
Operating and Storage Temperature Range	T _{stg}	- 65 to +175	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 300 mA	V _F	1.2	V
Peak Reverse Current at $V_R = 50 \text{ V}$	I _R	100	nA
Reverse Recovery Time at $I_F = I_R = 10$ to 200 mA, to 0.1 I_F	t _{rr}	4	ns









